

Atsushi Masuda

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

217
papers

2,960
citations

29
h-index

40
g-index

231
ext. papers

3,348
ext. citations

2.5
avg, IF

5.18
L-index

#	Paper	IF	Citations
217	Effect of temperature and pre-annealing on the potential-induced degradation of silicon heterojunction photovoltaic modules. <i>Japanese Journal of Applied Physics</i> , 2022 , 61, SC1021	1.4	0
216	Potential-Induced Degradation in High-Efficiency n-Type Crystalline-Silicon Photovoltaic Modules: A Literature Review. <i>Solar Rrl</i> , 2021 , 5, 2100708	7.1	1
215	Fabrication of Tantalum-Doped Titanium-Oxide Electron-Selective Contacts with High Passivation Quality. <i>ECS Journal of Solid State Science and Technology</i> , 2021 , 10, 045009	2	1
214	Influence of Light Irradiation on Potential-Induced Degradation for Thin-Film Si Photovoltaic Modules. <i>ECS Journal of Solid State Science and Technology</i> , 2021 , 10, 065018	2	
213	Influence of light illumination on the potential-induced degradation of n-type interdigitated back-contact crystalline Si photovoltaic modules. <i>Japanese Journal of Applied Physics</i> , 2021 , 60, SBBF08	1.4	3
212	Effects of passivation configuration and emitter surface doping concentration on polarization-type potential-induced degradation in n-type crystalline-silicon photovoltaic modules. <i>Solar Energy Materials and Solar Cells</i> , 2021 , 226, 111074	6.4	4
211	Study on photo-degradation of inverted organic solar cells caused by generation of potential barrier between PEDOT:PSS and PBDB-Ts. <i>Sustainable Energy and Fuels</i> , 2021 , 5, 3092-3096	5.8	2
210	A scanning nonlinear dielectric microscopic investigation of potential-induced degradation in monocrystalline silicon solar cells. <i>Applied Physics Letters</i> , 2020 , 116, 182107	3.4	0
209	A single-phase brookite TiO ₂ nanoparticle bridge enhances the stability of perovskite solar cells. <i>Sustainable Energy and Fuels</i> , 2020 , 4, 2009-2017	5.8	19
208	Elucidating the mechanism of potential induced degradation delay effect by ultraviolet light irradiation for p-type crystalline silicon solar cells. <i>Solar Energy</i> , 2020 , 199, 55-62	6.8	7
207	Temperature coefficient of the characteristic values of the charge-accumulation-type potential-induced-degraded n-type mono-crystalline silicon photovoltaic cell. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, 051001	1.4	
206	Influence of hygrothermal stress on potential-induced degradation for homojunction and heterojunction crystalline Si photovoltaic modules. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, 076503	1.4	4
205	Effect of a silicon nitride film on the potential-induced degradation of n-type front-emitter crystalline silicon photovoltaic modules. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, 104002	1.4	5
204	Characteristics change in organic photovoltaics by thermal recovery and photodegradation. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, SCCD04	1.4	1
203	Effect of a SiO ₂ film on the potential-induced degradation of n-type front-emitter crystalline Si photovoltaic modules. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, SCCD02	1.4	6
202	Influence of emitter position of silicon heterojunction photovoltaic solar cell modules on their potential-induced degradation behaviors. <i>Solar Energy Materials and Solar Cells</i> , 2020 , 216, 110716	6.4	6
201	Potential-induced degradation in photovoltaic modules composed of interdigitated back contact solar cells in photovoltaic systems under actual operating conditions. <i>Progress in Photovoltaics: Research and Applications</i> , 2020 , 28, 1322-1332	6.8	6

200	Universal explanation for degradation by charge accumulation in crystalline Si photovoltaic modules with application of high voltage. <i>Applied Physics Express</i> , 2019 , 12, 101003	2.4	4
199	Influence of backsheet materials on potential-induced degradation in n-type crystalline-silicon photovoltaic cell modules. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, 120901	1.4	1
198	Effect of additives in electrode paste of p-type crystalline Si solar cells on potential-induced degradation. <i>Solar Energy</i> , 2019 , 188, 1292-1297	6.8	6
197	Influence of sodium on the potential-induced degradation for n-type crystalline silicon photovoltaic modules. <i>Applied Physics Express</i> , 2019 , 12, 064004	2.4	8
196	Similarity of potential-induced degradation in superstrate-type thin-film CdTe and Si photovoltaic modules. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, SBBF07	1.4	6
195	Investigation of UV and hygrothermal stress on back side of rack-mounted photovoltaic modules. <i>Renewable Energy Focus</i> , 2019 , 29, 107-113	5.4	2
194	Investigation of the power generation of organic photovoltaic modules connected to the power grid for more than three years. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, 052001	1.4	5
193	Corrosion-Induced AC Impedance Elevation in Front Electrodes of Crystalline Silicon Photovoltaic Cells Within Field-Aged Photovoltaic Modules. <i>IEEE Journal of Photovoltaics</i> , 2019 , 9, 741-751	3.7	4
192	Temperature dependence of potential-induced degraded p-type mono-crystalline silicon photovoltaic cell characteristics. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, 101005	1.4	2
191	Output power behavior of passivated emitter and rear cell photovoltaic modules during early installation stage: influence of light-induced degradation. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, 106510	1.4	1
190	Corrections to Corrosion-Induced AC Impedance Elevation in Front Electrodes of Crystalline Silicon Photovoltaic Cells Within Field-Aged Photovoltaic Modules <i>IEEE Journal of Photovoltaics</i> , 2019 , 9, 1154-1154	3.7	0
189	Durable crystalline Si photovoltaic modules based on silicone-sheet encapsulants. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 027101	1.4	8
188	Bending cyclic load test for crystalline silicon photovoltaic modules. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 02CE05	1.4	5
187	Comprehensive study of potential-induced degradation in silicon heterojunction photovoltaic cell modules. <i>Progress in Photovoltaics: Research and Applications</i> , 2018 , 26, 697-708	6.8	18
186	Multistage performance deterioration in n-type crystalline silicon photovoltaic modules undergoing potential-induced degradation. <i>Microelectronics Reliability</i> , 2018 , 84, 127-133	1.2	17
185	Effect of bias voltage application on potential-induced degradation for crystalline silicon photovoltaic modules. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 08RG01	1.4	4
184	Performance degradation due to outdoor exposure and seasonal variation in amorphous silicon photovoltaic modules. <i>Thin Solid Films</i> , 2018 , 661, 116-121	2.2	11
183	Accurate measurement and estimation of solar cell temperature in photovoltaic module operating in real environmental conditions. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 08RG08	1.4	7

182	Lamination-interface-dependent deacetylation of ethylene vinyl acetate encapsulant in crystalline Si photovoltaic modules evaluated by positron annihilation lifetime spectroscopy. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 082301	1.4	1
181	Localization and Characterization of a Degraded Site in Crystalline Silicon Photovoltaic Cells Exposed to Acetic Acid Vapor. <i>IEEE Journal of Photovoltaics</i> , 2018 , 8, 997-1004	3.7	13
180	Detection of acetic acid produced in photovoltaic modules based on tin film corrosion during damp heat test. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 08RG16	1.4	5
179	Sodium distribution at the surface of silicon nitride film after potential-induced degradation test and recovery test of photovoltaic modules. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 08RG05	1.4	2
178	Exploring suitable damp heat and potential induced degradation test procedures for Cu(In,Ga)(S,Se) photovoltaic modules. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 08RG02	1.4	7
177	Overall analysis of change in power generation with outdoor exposure of photovoltaic modules installed at AIST Kyushu Center. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 08RG04	1.4	6
176	Soiling by volcanic ash fall on photovoltaic modules and effects of hydrophilic coating on module cover glass. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 08RG06	1.4	1
175	Effect of barrier property of backsheets on degradation of crystalline silicon photovoltaic modules under combined acceleration test composed of UV irradiation and subsequent damp-heat stress. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 127101	1.4	0
174	Origin of Na causing potential-induced degradation for p-type crystalline Si photovoltaic modules. <i>AIP Advances</i> , 2018 , 8, 115311	1.5	6
173	Rapid progression and subsequent saturation of polarization-type potential-induced degradation of n-type front-emitter crystalline-silicon photovoltaic modules. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 122301	1.4	13
172	Annual Degradation Rates of Recent c-Si PV Modules under Subtropical Coastal Climate Conditions 2018 ,		2
171	Potential-induced degradation of n-type crystalline Si photovoltaic modules in practical outdoor systems. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 117102	1.4	4
170	Accelerated Outdoor PID Testing of CIGS Modules and Comparison with Indoor PID Tests 2018 ,		1
169	Effect of light irradiation during potential-induced degradation tests for p-type crystalline Si photovoltaic modules. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 08RG13	1.4	7
168	Reliability and long term durability of bifacial photovoltaic modules using transparent backsheets. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 08RG15	1.4	4
167	Temperature dependence measurements and performance analyses of high-efficiency interdigitated back-contact, passivated emitter and rear cell, and silicon heterojunction photovoltaic modules. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 08RG18	1.4	11
166	Guiding principle for crystalline Si photovoltaic modules with high tolerance to acetic acid. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 04FS06	1.4	4
165	Influence of surface structure of n-type single-crystalline Si solar cells on potential-induced degradation. <i>Solar Energy Materials and Solar Cells</i> , 2017 , 166, 132-139	6.4	24

164	Reduction in the short-circuit current density of silicon heterojunction photovoltaic modules subjected to potential-induced degradation tests. <i>Solar Energy Materials and Solar Cells</i> , 2017 , 161, 439-443	6.4	26
163	Causes of Degradation Identified by the Extended Thermal Cycling Test on Commercially Available Crystalline Silicon Photovoltaic Modules. <i>IEEE Journal of Photovoltaics</i> , 2017 , 7, 1511-1518	3.7	21
162	Development of a practical method of estimating electric power from various photovoltaic technologies with high precision. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 08MD05	1.4	2
161	Annual degradation rates of recent crystalline silicon photovoltaic modules. <i>Progress in Photovoltaics: Research and Applications</i> , 2017 , 25, 953-967	6.8	54
160	Potential-induced degradation of thin-film Si photovoltaic modules. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 04CS04	1.4	9
159	Effect of light irradiation and forward bias during PID tests of CIGS PV modules 2017 ,		1
158	Time-dependent changes in copper indium gallium (di)selenide and cadmium telluride photovoltaic modules due to outdoor exposure. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 08MD06	1.4	3
157	Progression of rapid potential-induced degradation of n-type single-crystalline silicon photovoltaic modules. <i>Applied Physics Express</i> , 2016 , 9, 112301	2.4	20
156	Effects of UV on power degradation of photovoltaic modules in combined acceleration tests. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 052301	1.4	13
155	Issues and Solutions Concerned in the Coefficient of Thermal Expansion on Photovoltaic Modules. <i>Hyomen Gijutsu/Journal of the Surface Finishing Society of Japan</i> , 2016 , 67, 146-148	0.1	
154	Acceleration of degradation by highly accelerated stress test and air-included highly accelerated stress test in crystalline silicon photovoltaic modules. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 022302	1.4	9
153	Changes in the current density, voltage and external quantum efficiency characteristics of n-type single-crystalline silicon photovoltaic modules with a rear-side emitter undergoing potential-induced degradation. <i>Solar Energy Materials and Solar Cells</i> , 2016 , 151, 113-119	6.4	38
152	Consideration on Na diffusion and recovery phenomena in potential-induced degradation for crystalline Si photovoltaic modules. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 02BF10	1.4	14
151	Sequential and combined acceleration tests for crystalline Si photovoltaic modules. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 04ES10	1.4	12
150	Behavior of the potential-induced degradation of photovoltaic modules fabricated using flat mono-crystalline silicon cells with different surface orientations. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 04ES14	1.4	5
149	Degradation of encapsulants for photovoltaic modules made of ethylene vinyl acetate studied by positron annihilation lifetime spectroscopy. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 102302	1.4	3
148	Potential-induced degradation behavior of n-type single-crystalline silicon photovoltaic modules with a rear-side emitter 2016 ,		3
147	Proposed new damp heat test standards for commercial CIGS modules with bias application or light irradiation 2016 ,		3

146	Direct evidence for pn junction without degradation in crystalline Si photovoltaic modules under hygrothermal stresses 2016 ,		3
145	Electrical detection of gap formation underneath finger electrodes on c-Si PV cells exposed to acetic acid vapor under hygrothermal conditions 2016 ,		11
144	Microscopic aspects of potential-induced degradation phenomena and their recovery processes for p-type crystalline Si photovoltaic modules. <i>Current Applied Physics</i> , 2016 , 16, 1659-1665	2.6	27
143	Multi angle laser light scattering evaluation of field exposed thermoplastic photovoltaic encapsulant materials. <i>Energy Science and Engineering</i> , 2016 , 4, 40-51	3.4	9
142	Potential-induced degradation of Cu(In,Ga)Se ₂ photovoltaic modules. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 08KC13	1.4	44
141	Crystalline Si photovoltaic modules functionalized by a thin polyethylene film against potential and damp-heat-induced degradation. <i>RSC Advances</i> , 2015 , 5, 15017-15023	3.7	28
140	Potential-induced degradation in photovoltaic modules based on n-type single crystalline Si solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2015 , 140, 361-365	6.4	62
139	Module composition for reliability test of organic photovoltaics. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 08KF07	1.4	1
138	Relationship between cross-linking conditions of ethylene vinyl acetate and potential induced degradation for crystalline silicon photovoltaic modules. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 08KG01	1.4	29
137	Field testing of thermoplastic encapsulants in high-temperature installations. <i>Energy Science and Engineering</i> , 2015 , 3, 565-580	3.4	23
136	Acceleration of potential-induced degradation by salt-mist preconditioning in crystalline silicon photovoltaic modules. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 08KG08	1.4	14
135	Plasma-enhanced chemical-vapor deposition of silicon nitride film for high resistance to potential-induced degradation. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 08KD12	1.4	12
134	Degradation by acetic acid for crystalline Si photovoltaic modules. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 04DR04	1.4	27
133	Effects of light illumination during damp/dry heat tests on a flexible thin film photovoltaic module 2015 ,		2
132	Development of a pH sensor based on a nanostructured filter adding pH-sensitive fluorescent dye for detecting acetic acid in photovoltaic modules. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 08KG07	1.4	6
131	Crystalline Si photovoltaic modules based on TiO ₂ -coated cover glass against potential-induced degradation. <i>RSC Advances</i> , 2014 , 4, 44291-44295	3.7	43
130	Investigation on antireflection coating for high resistance to potential-induced degradation. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 03CE01	1.4	29
129	Novel lighter weight crystalline silicon photovoltaic module using acrylic-film as a cover sheet. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 092302	1.4	30

128	Detection of acid moisture in photovoltaic modules using a dual wavelength pH-sensitive fluorescent dye. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 04ER18	1.4	7
127	Recent Situation and Future Prospects of Photovoltaic Industries and Technologies. <i>Journal of the Vacuum Society of Japan</i> , 2012 , 55, 520-528		
126	Microscopic Degradation Mechanisms in Silicon Photovoltaic Module under Long-Term Environmental Exposure. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 10NF07	1.4	12
125	Early Failure Detection of Interconnection with Rapid Thermal Cycling in Photovoltaic Modules. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 10NF13	1.4	3
124	Measuring Method of Moisture Ingress into Photovoltaic Modules. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 10NF12	1.4	4
123	Microscopic Degradation Mechanisms in Silicon Photovoltaic Module under Long-Term Environmental Exposure. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 10NF07	1.4	13
122	Measuring Method of Moisture Ingress into Photovoltaic Modules. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 10NF12	1.4	7
121	Early Failure Detection of Interconnection with Rapid Thermal Cycling in Photovoltaic Modules. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 10NF13	1.4	5
120	Recent Situation and Future Prospects of Photovoltaics. <i>Nippon Gomu Kyokaishi</i> , 2011 , 84, 153-160	0	
119	Study on silicon-slicing technique using plasma-etching processing. <i>Solar Energy Materials and Solar Cells</i> , 2009 , 93, 789-791	6.4	9
118	Investigation on the crystal growth process of spherical Si single crystals by melting. <i>Journal of Crystal Growth</i> , 2009 , 311, 4116-4122	1.6	11
117	Epitaxial Growth of SiC on Silicon on Insulator Substrates with Ultrathin Top Si Layer by Hot-Mesh Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , 2008 , 47, 569-572	1.4	5
116	Formation of Low-Defect-Concentration Polycrystalline Silicon Films by Thermal Plasma Jet Crystallization Technique. <i>Japanese Journal of Applied Physics</i> , 2008 , 47, 6949-6952	1.4	15
115	Investigating minority-carrier lifetime in small spherical Si using microwave photoconductance decay. <i>Journal of Applied Physics</i> , 2008 , 103, 104909	2.5	6
114	Improvement of the uniformity in electronic properties of AZO films using an rf magnetron sputtering with a mesh grid electrode. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2008 , 148, 26-29	3.1	11
113	Coverage properties of SiNx films prepared by catalytic chemical vapor deposition on trenched substrates below 800°C. <i>Thin Solid Films</i> , 2008 , 516, 3000-3004	2.2	2
112	Cat-CVD SiN passivation films for OLEDs and packaging. <i>Thin Solid Films</i> , 2008 , 516, 553-557	2.2	21
111	A concentrator module of spherical Si solar cell. <i>Solar Energy Materials and Solar Cells</i> , 2007 , 91, 1805-1810	6.4	21

110	Improvement of the Production Yield of Spherical Si by Optimization of the Seeding Technique in the Dropping Method. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, 5695-5700	1.4	7
109	Defect Reduction in Polycrystalline Silicon Thin Films by Heat Treatment with High-Pressure H ₂ O Vapor. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, 1286-1289	1.4	18
108	Characterization of spherical Si by photoluminescence measurement. <i>Journal of Applied Physics</i> , 2007 , 101, 103530	2.5	8
107	Seeding method with silicon powder for the formation of silicon spheres in the drop method. <i>Journal of Applied Physics</i> , 2007 , 101, 093505	2.5	17
106	Various applications of silicon nitride by catalytic chemical vapor deposition for coating, passivation and insulating films. <i>Thin Solid Films</i> , 2006 , 501, 149-153	2.2	28
105	Formation of highly moisture-resistive SiN _x films on Si substrate by Cat-CVD at room temperature. <i>Thin Solid Films</i> , 2006 , 501, 154-156	2.2	6
104	Preparation of SiN _x gate-insulating films for bottom-gate type TFTs by Cat-CVD method. <i>Thin Solid Films</i> , 2006 , 501, 307-309	2.2	
103	Grain Enlargement of Polycrystalline Silicon by Multipulse Excimer Laser Annealing: Role of Hydrogen. <i>Japanese Journal of Applied Physics</i> , 2006 , 45, 2726-2730	1.4	17
102	Mass-Spectrometric Studies of Catalytic Chemical Vapor Deposition Processes of Organic Silicon Compounds Containing Nitrogen. <i>Japanese Journal of Applied Physics</i> , 2006 , 45, 961-966	1.4	15
101	H ₂ dilution effect in the Cat-CVD processes of the SiH ₄ /NH ₃ system. <i>Thin Solid Films</i> , 2006 , 501, 31-34	2.2	19
100	Systematic study on photoresist removal using hydrogen atoms generated on heated catalyzer. <i>Thin Solid Films</i> , 2006 , 501, 326-328	2.2	31
99	Present status and future feasibility for industrial implementation of Cat-CVD (Hot-Wire CVD) technology. <i>Thin Solid Films</i> , 2006 , 501, 58-60	2.2	31
98	High-rate deposition of SiN _x films over 100 nm/min by Cat-CVD method at low temperatures below 80 °C. <i>Thin Solid Films</i> , 2006 , 501, 55-57	2.2	7
97	Low-Temperature Deposition of Silicon Nitride Films by a Cat-CVD Technique-Gas-Phase Diagnoses and Evaluation of Film Properties-. <i>Zairyo/Journal of the Society of Materials Science, Japan</i> , 2006 , 55, 142-147	0.1	
96	Preparation of Low-Stress SiN _x Films by Catalytic Chemical Vapor Deposition at Low Temperatures. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, 4098-4102	1.4	11
95	Quantification of Gas-Phase H-Atom Number Density by Tungsten Phosphate Glass. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, 732-735	1.4	25
94	Moisture-Resistive Properties of SiN _x Films Prepared by Catalytic Chemical Vapor Deposition below 100°C for Flexible Organic Light-Emitting Diode Displays. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, 1923-1927	1.4	8
93	Technique for the production, preservation, and transportation of H atoms in metal chambers for processings. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2005 , 23, 1728-1731 ^{2,9}		20

92	Air-stable n-type carbon nanotube field-effect transistors with Si ₃ N ₄ passivation films fabricated by catalytic chemical vapor deposition. <i>Applied Physics Letters</i> , 2005 , 86, 113115	3.4	80
91	Effect of Atomic Hydrogen on Preparation of Highly Moisture-Resistive SiN _x Films at Low Substrate Temperatures. <i>Japanese Journal of Applied Physics</i> , 2004 , 43, L1546-L1548	1.4	11
90	Correlation between O/Er Content Ratio and Photoluminescence Intensity of (Er, O)-Doped Hydrogenated Amorphous Si Thin Films Prepared by a Catalytic Chemical Vapor Deposition/Laser Ablation Hybrid Process. <i>Japanese Journal of Applied Physics</i> , 2004 , 43, 4198-4201	1.4	2
89	Highly Moisture-Resistive SiN _x Films Prepared by Catalytic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , 2004 , 43, L1362-L1364	1.4	19
88	Nitridation of Ultrathin SiO ₂ Layers in Metal-Ferroelectric-Insulator-Semiconductor Structures. <i>Integrated Ferroelectrics</i> , 2004 , 68, 29-36	0.8	1
87	Highly moisture-resistive silicon nitride films prepared by catalytic chemical vapor deposition and application to gallium arsenide field-effect transistors. <i>Vacuum</i> , 2004 , 74, 525-529	3.7	20
86	Study on change in SIMS intensities near the interface between silicon-nitride film and silicon substrate. <i>Applied Surface Science</i> , 2004 , 231-232, 725-728	6.7	4
85	Cat-CVD (hot-wire CVD): how different from PECVD in preparing amorphous silicon. <i>Journal of Non-Crystalline Solids</i> , 2004 , 338-340, 19-26	3.9	33
84	Catalytic decomposition of HCN on heated W surfaces to produce CN radicals. <i>Journal of Non-Crystalline Solids</i> , 2004 , 338-340, 65-69	3.9	10
83	Catalytic Chemical Vapor Deposition of a-Si:H TFT 2004 , 377-394		
82	Radical Species Formed by the Catalytic Decomposition of NH ₃ on Heated W Surfaces. <i>Japanese Journal of Applied Physics</i> , 2003 , 42, 5315-5321	1.4	53
81	57.1: Invited Paper: Present Status of Cat-CVD as a New Fabrication Technology for Large Area Display. <i>Digest of Technical Papers SID International Symposium</i> , 2003 , 34, 1504	0.5	
80	Development of Cat-CVD apparatus for 1-m-size large-area deposition. <i>Thin Solid Films</i> , 2003 , 430, 58-62	2.2	25
79	Fabrication of a-Si _{1-x} C _x H thin films for solar cells by the Cat-CVD method using a carbon catalyzer. <i>Thin Solid Films</i> , 2003 , 430, 170-173	2.2	7
78	Deposition chemistry in the Cat-CVD processes of the SiH ₄ /NH ₃ system. <i>Thin Solid Films</i> , 2003 , 430, 24-27	2.2	35
77	Recent progress of Cat-CVD research in Japan—Bridging between the first and second Cat-CVD conferences. <i>Thin Solid Films</i> , 2003 , 430, 7-14	2.2	31
76	Crystallization by excimer laser annealing for a-Si:H films with low hydrogen content prepared by Cat-CVD. <i>Thin Solid Films</i> , 2003 , 430, 296-299	2.2	12
75	Properties of High Quality p-Type Micro-Crystalline-Si Prepared by Cat-CVD. <i>Materials Research Society Symposia Proceedings</i> , 2003 , 762, 1321		1

74	Properties of Phosphorus-Doped Polycrystalline Silicon Films Formed by Catalytic Chemical Vapor Deposition and Successive Rapid Thermal Annealing 2003 , 63-68		
73	Catalytic Chemical Vapor Deposition Recent Development and Future Prospects. <i>Shinku/Journal of the Vacuum Society of Japan</i> , 2003 , 46, 92-97		1
72	Recent Progress in Industrial Applications of CAT-CVD (Hot-Wire Cvd). <i>Materials Research Society Symposia Proceedings</i> , 2002 , 715, 1741		7
71	In situ chamber cleaning using atomic H in catalytic-CVD apparatus for mass production of a-Si:H solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2002 , 74, 373-377	6.4	7
70	Influence of atomic hydrogen on transparent conducting oxides during hydrogenated amorphous and microcrystalline Si preparation by catalytic chemical vapor deposition. <i>Thin Solid Films</i> , 2002 , 411, 166-170	2.2	11
69	What is the difference between catalytic CVD and plasma-enhanced CVD? Gas-phase kinetics and film properties. <i>Vacuum</i> , 2002 , 66, 293-297	3.7	5
68	Low-Resistivity Phosphorus-Doped Polycrystalline Silicon Thin Films Formed by Catalytic Chemical Vapor Deposition and Successive Rapid Thermal Annealing. <i>Japanese Journal of Applied Physics</i> , 2002 , 41, 501-506	1.4	14
67	Effects of atomic hydrogen in gas phase on a-Si:H and poly-Si growth by catalytic CVD. <i>Journal of Non-Crystalline Solids</i> , 2002 , 299-302, 9-13	3.9	23
66	Direct detection of H atoms in the catalytic chemical vapor deposition of the SiH ₄ /H ₂ system. <i>Journal of Applied Physics</i> , 2002 , 91, 1650-1656	2.5	140
65	Development of Large-Area Uniform Deposition Technique on 1-m-Size Substrate by Catalytic Chemical Vapor Deposition.. <i>Shinku/Journal of the Vacuum Society of Japan</i> , 2002 , 45, 123-126		2
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